INTEGRATED CIRCUITS

DATA SHEET



74LVT003.3V Quad 2-input NAND gate

Product specification

1996 Aug 15

IC24 Data Handbook





3.3V Quad 2-input NAND gate

74LVT00

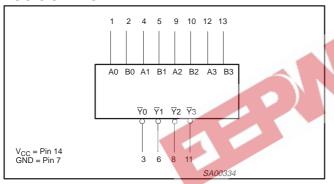
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
^t РLН ^t РНL	Propagation delay An or Bn to \(\forall n\)	C _L = 50pF; V _{CC} = 3.3V	2.7 2.7	ns
C _{IN}	Input capacitance	V _I = 0V or 3.0V	3	pF
I _{CCL}	Total supply current	Outputs Low; V _{CC} = 3.6V	1	mA

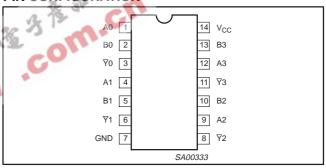
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER	
14-Pin Plastic SO	-40°C to +85°C	74LVT00 D	74LVT00 D	SOT108-1	
14-Pin Plastic SSOP	-40°C to +85°C	74LVT00 DB	74LVT00 DB	SOT337-1	
14-Pin Plastic TSSOP	-40°C to +85°C	74LVT00 PW	74LVT00PW DH	SOT402-1	

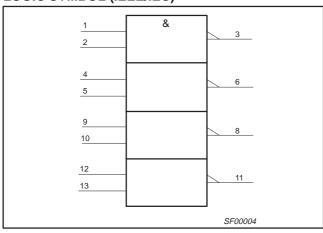
LOGIC SYMBOL



PIN CONFIGURATION



LOGIC SYMBOL (IEEE/IEC)



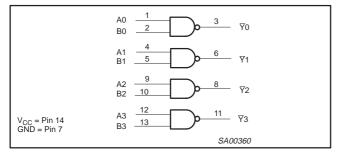
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 2, 4, 5, 9, 10, 12, 13	An-Bn	Data inputs
3, 6, 8, 11	₹n	Data outputs
7	GND	Ground (0V)
14	V _{CC}	Positive supply voltage

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LOGIC DIAGRAM



FUNCTION TABLE

INP	UTS	OUTPUT			
Dna	Dnb	Qn			
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			

NOTES:

H = High voltage level L = Low voltage level

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +4.6	V
I _{IK}	DC input diode current	V _I < 0	-50	mA
VI	DC input voltage ³	4,45 /4	-0.5 to +7.0	V
I _{OK}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	Output in Off or High state	-0.5 to +7.0	V
	DC output current	Output in High state	-32	mA
I _{OUT}	DC output current	Output in Low state	64	l IIIA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 The performance capability of a high-performance integrated or in conjunction with its thermal environment can create junction
- temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- 3. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	ITS	UNIT
STIMBUL	PARAMETER	MIN	MAX	UNIT
V _{CC}	DC supply voltage	2.7	3.6	V
VI	Input voltage	0	5.5	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level Input voltage		0.8	V
I _{OH}	High-level output current		-20	mA
I _{OL}	Low-level output current		32	mA
Δt/Δν	Input transition rise or fall rate; Outputs enabled	·	10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions Voltages are referenced to GND (ground = 0V)

			ı	IMITS		
SYMBOL	PARAMETER	TEST CONDITIONS	Temp = -	+85°C	UNIT	
			MIN TYP ¹ MA		MAX	
V _{IK}	Input clamp voltage	$V_{CC} = 2.7V; I_{IK} = -18mA$			-1.2	V
		$V_{CC} = 2.7 \text{ to } 3.6V; I_{OH} = -100 \mu\text{A}$	V _{CC} -0.2			
V_{OH}	High-level output voltage	V _{CC} = 2.7V; I _{OH} = -6mA	2.4			V
		$V_{CC} = 3.0V; I_{OH} = -20mA$	2.0			
		V _{CC} = 2.7V; I _{OL} = 100μA			0.2	
V_{OL}	Low-level output voltage	V _{CC} = 2.7V; I _{OL} = 24mA			0.5	V
		V _{CC} = 3.0V; I _{OL} = 32mA			0.5	
1.	Input lookogo gurrant	V _{CC} = 0 or 3.6V; V _I = 5.5V			10	^
1 ₁	Input leakage current	V_{CC} = 3.6V; V_{I} = V_{CC} or GND			±1	μА
I_{OFF}	Output off current	$V_{CC} = 0V$; V_{I} or $V_{O} = 0$ to 4.5V			±100	μΑ
I _{CCH}	Ouisecont cumply current	$V_{CC} = 3.6V$; Outputs High, $V_{I} = GND$ or V_{CC} , $I_{O} = 0$			0.02	mA
I _{CCL}	Quiescent supply current	V_{CC} = 3.6V; Outputs Low, V_{I} = GND or V_{CC} , I_{C} = 0		1	2	IIIA
Δl _{CC}	Additional supply current per input pin ²	V_{CC} = 3V to 3.6V; One input at V_{CC} –0.6V, Other inputs at V_{CC} or GND			0.2	μА
Cl	Input capacitance	$V_I = 3V \text{ or } 0$		3		pF

NOTES:

- All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.
 This is the increase in supply current for each input at the specificed voltage level other than V_{CC} or GND.

AC CHARACTERISTICS

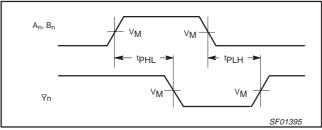
GND = 0V; $t_R = t_F$ = 2.5ns; C_L = 50pF, R_L = 500 Ω ; T_{amb} = -40°C to +85°C.

				LI	MITS		
SYMBOL	PARAMETER	WAVEFORM	Vcc	$= 3.3 V \pm 0$.3V	V _{CC} = 2.7V	UNIT
			MIN	TYP ¹	MAX	MAX	
t _{PLH} t _{PHL}	Propagation delay An or Bn to ∀n	1	1.0 1.0	2.7 2.7	4.1 3.9	5.0 3.8	ns

1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

AC WAVEFORMS

 $V_{M} = 1.5V_{,} V_{IN} = GND \text{ to } 2.7V$



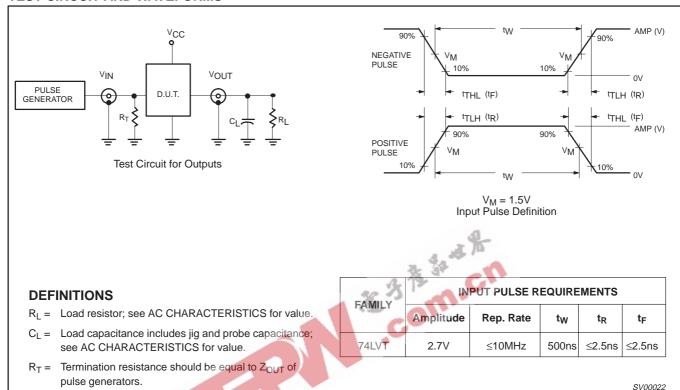
Waveform 1. Propagation delay for inverting outputs

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TEST CIRCUIT AND WAVEFORMS

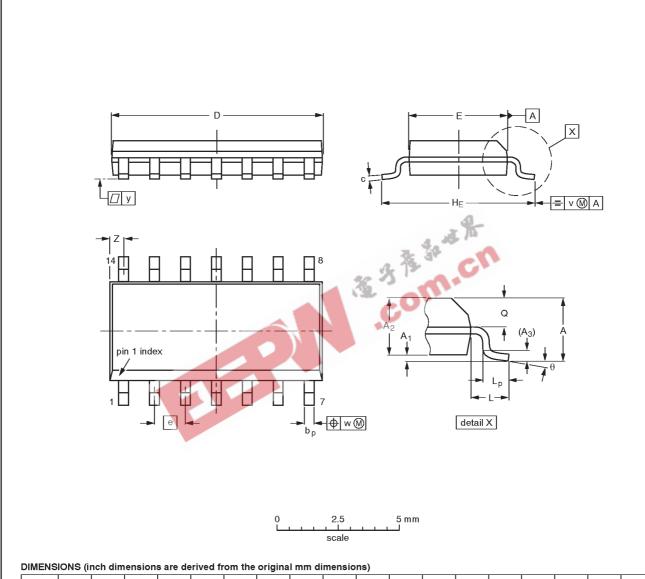


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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	Α1	A ₂	A ₃	рb	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	L വ വടവ	0.0098 0.0039		0.01	0.019 0.014	0.0098 0.0075		0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

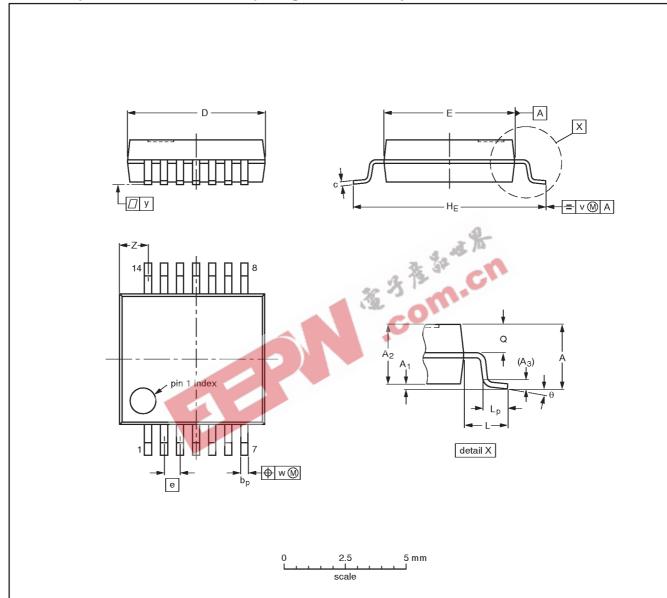
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT108-1	076E06\$	MS-012AB				91-08-13- 95-01-23	

3.3V Quad 2-input NAND gate

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

						-,												
UNIT	A max.	Α ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

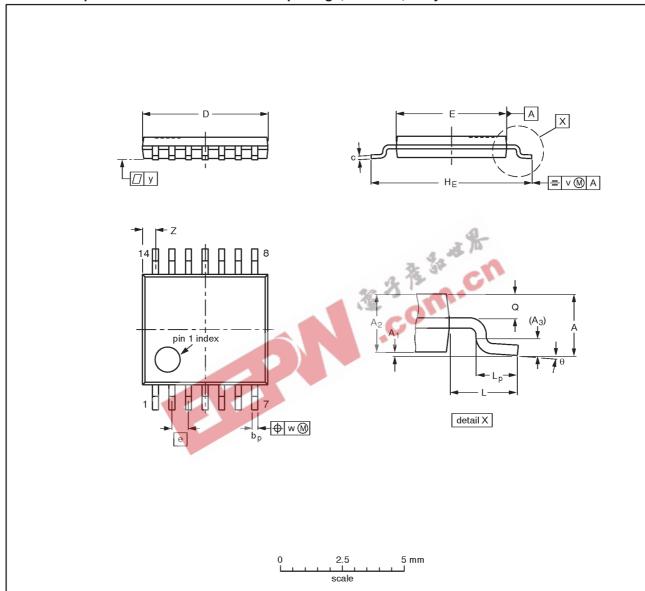
OUTLINE		EUROPEAN	ISSUE DATE		
VERSION	VERSION IEC JEDEC EIAJ		PROJECTION	ISSUE DATE	
SOT337-1		MO-150AB			-95-02-04 96-01-18

3.3V Quad 2-input NAND gate

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	A ₃	рb	С	D (1)	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION		REFER	EUROPEAN	ICCUE DATE		
	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT402-1		MO-153				-94-07-12 95-04-04

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NOTES



3.3V Quad 2-input NAND gate

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DEFINITIONS						
Data Sheet Identification	Product Status	Definition				
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